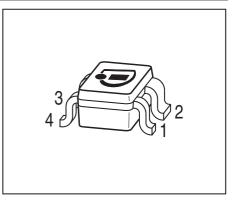


BFP540

Low Noise Silicon Bipolar RF Transistor

- For highest gain and low noise amplifier
- Outstanding G_{ms} = 21.5 dB at 1.8 GHz Minimum noise figure NF_{min} = 0.9 dB at 1.8 GHz
- Pb-free (RoHS compliant) and halogen-free package with visible leads
- Qualification report according to AEC-Q101 available





ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration					Package	
BFP540	ATs	1=B	2=E	3=C	4=E	-	-	SOT343

Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Collector-emitter voltage	V _{CEO}		V	
<i>T</i> _A = 25 °C		4.5		
<i>T</i> _A = -55 °C		4		
Collector-emitter voltage	V _{CES}	14		
Collector-base voltage	V _{CBO}	14		
Emitter-base voltage	V _{EBO}	1		
Collector current	I _C	80	mA	
Base current	I _B	8		
Total power dissipation ¹⁾	P _{tot}	250	mW	
_ <i>T</i> _S ≤ 77°C				
Junction temperature	TJ	150	°C	
Ambient temperature	T _A	-65 150		
Storage temperature	T _{Stq}	-65 150		

 $^{1}\mathcal{T}_{S}$ is measured on the emitter lead at the soldering point to the pcb



Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R _{thJS}	290	K/W

Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.]
DC Characteristics					•
Collector-emitter breakdown voltage	V _{(BR)CEO}	4.5	5	-	V
<i>I</i> _C = 1 mA, <i>I</i> _B = 0					
Collector-emitter cutoff current	I _{CES}	-	-	10	μA
$V_{\rm CE}$ = 14 V, $V_{\rm BE}$ = 0					
Collector-base cutoff current	I _{CBO}	-	-	100	nA
$V_{\rm CB} = 5 \text{V}, I_{\rm E} = 0$					
Emitter-base cutoff current	I _{EBO}	-	-	10	μA
$V_{\rm EB}$ = 0.5 V, $I_{\rm C}$ = 0					
DC current gain	h _{FE}	50	110	185	-
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 3.5 V, pulse measured					

¹For the definition of R_{thJS} please refer to Application Note AN077 (Thermal Resistance Calculation)



Parameter	Symbol	Values			Unit	
		min.	typ.	max.		
AC Characteristics (verified by random sampling)						
Transition frequency	f _T	21	30	-	GHz	
$I_{\rm C}$ = 50 mA, $V_{\rm CE}$ = 4 V, f = 1 GHz						
Collector-base capacitance	C _{cb}	-	0.14	0.24	pF	
$V_{CB} = 2 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$,						
emitter grounded						
Collector emitter capacitance	C _{ce}	-	0.33	-		
$V_{CE} = 2 V, f = 1 MHz, V_{BE} = 0$,						
base grounded						
Emitter-base capacitance	C _{eb}	-	0.65	-		
$V_{\rm EB}$ = 0.5 V, f = 1 MHz, $V_{\rm CB}$ = 0 ,						
collector grounded						
Minimum noise figure	NF _{min}				dB	
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 2 V, f = 1.8 GHz, $Z_{\rm S}$ = $Z_{\rm Sopt}$		-	0.9	1.4		
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 2 V, f = 3 GHz, $Z_{\rm S}$ = $Z_{\rm Sopt}$		-	1.3	-		
Power gain, maximum stable ¹⁾	G _{ms}	-	21.5	-	dB	
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 2 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,						
$Z_{\rm L} = Z_{\rm Lopt}$, $f = 1.8 {\rm GHz}$						
Power gain, maximum available ¹⁾	G _{ma}	-	16	-	dB	
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 2 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,						
$Z_{\rm L} = Z_{\rm Lopt}, f = 3 \rm GHz$						
Transducer gain	S _{21e} ²				dB	
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 2 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,						
<i>f</i> = 1.8 GHz		16	18.5	-		
<i>f</i> = 3 GHz		-	14.5	-		
Third order intercept point at output ²⁾	IP3	-	24.5	-	dBm	
$V_{\rm CE}$ = 2 V, $I_{\rm C}$ = 20 mA, $Z_{\rm S}$ = $Z_{\rm L}$ =50 Ω , f = 1.8 GHz						
1dB compression point at output	P _{-1dB}	-	11	-		
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 2 V, $Z_{\rm S}$ = $Z_{\rm L}$ =50 Ω , f = 1.8 GHz						

Electrical Characteristics at T_A = 25 °C, unless otherwise specified

 ${}^{1}G_{ma} = |S_{21e} / S_{12e}| (k \cdot (k^{2} \cdot 1)^{1/2}), G_{ms} = |S_{21e} / S_{12e}|$

 $^2\mbox{IP3}$ value depends on termination of all intermodulation frequency components.

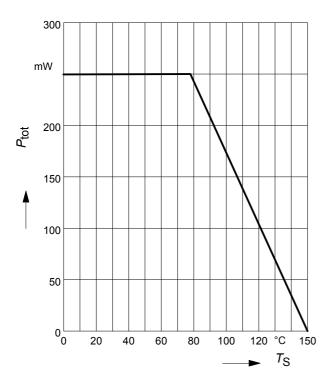
Termination used for this measurement is 50Ω from 0.1 MHz to 6 GHz



BFP540

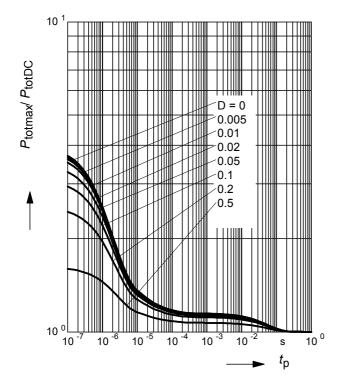
Total power dissipation $P_{tot} = f(T_S)$

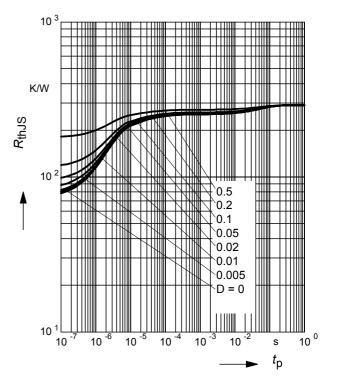
Permissible Pulse Load $R_{\text{thJS}} = f(t_p)$



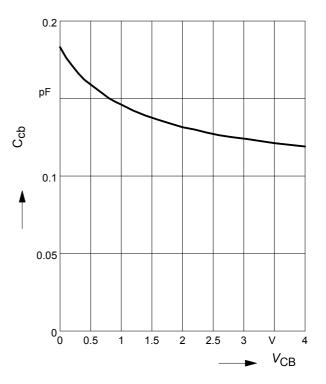
Permissible Pulse Load

 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$





Collector-base capacitance C_{CD} = $f(V_{CB})$ f = 1MHz

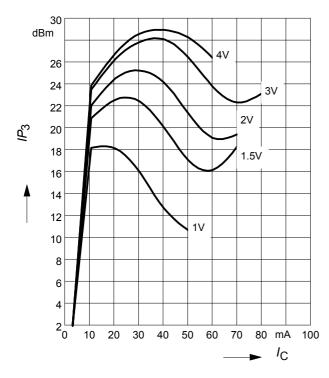




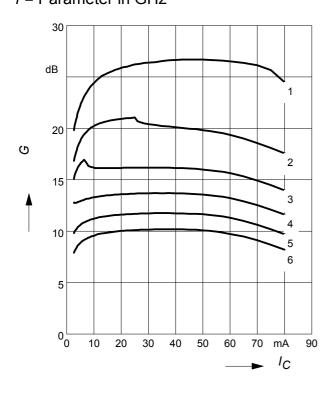
Third order Intercept Point $IP_3=f(I_C)$

(Output, $Z_S=Z_L=50\Omega$)

 V_{CE} = parameter, f = 1.8GHz



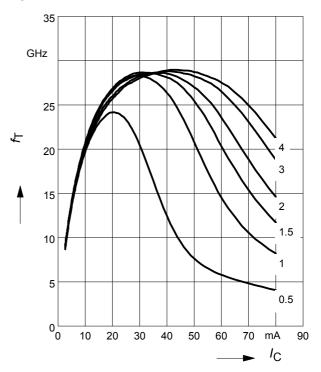
Power gain G_{ma} , $G_{ms} = f(I_C)$ $V_{CE} = 2V$ f = Parameter in GHz



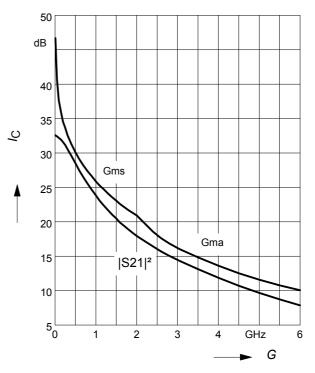
Transition frequency $f_{T} = f(I_{C})$

f = 1GHz

 V_{CE} = Parameter in V



Power Gain G_{ma} , $G_{ms} = f(f)$, $|S_{21}|^2 = f(f)$ $V_{CE} = 2V$, $I_C = 20mA$

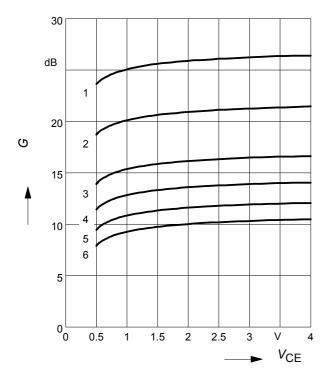




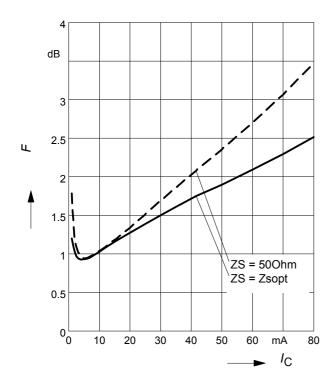
Power gain G_{ma} , $G_{ms} = f(V_{CE})$

*I*_C = 20mA

f = Parameter in GHz

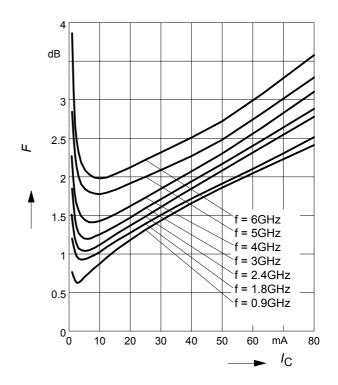


Noise figure $F = f(I_C)$ $V_{CE} = 2V, f = 1.8GHz$

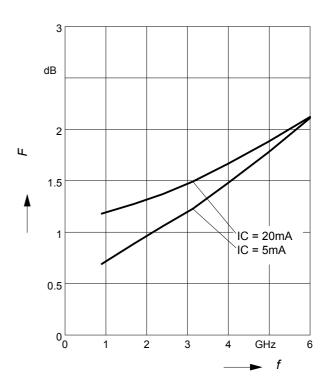


Noise figure $F = f(I_C)$

 V_{CE} = 2V, Z_S = Z_{Sopt}



Noise figure F = f(f) $V_{CE} = 2V, Z_S = Z_{Sopt}$

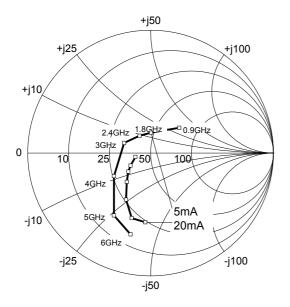




Source impedance for min.

noise figure vs. frequency

 $V_{\rm CE}$ = 2V, $I_{\rm C}$ = 5mA / 20mA



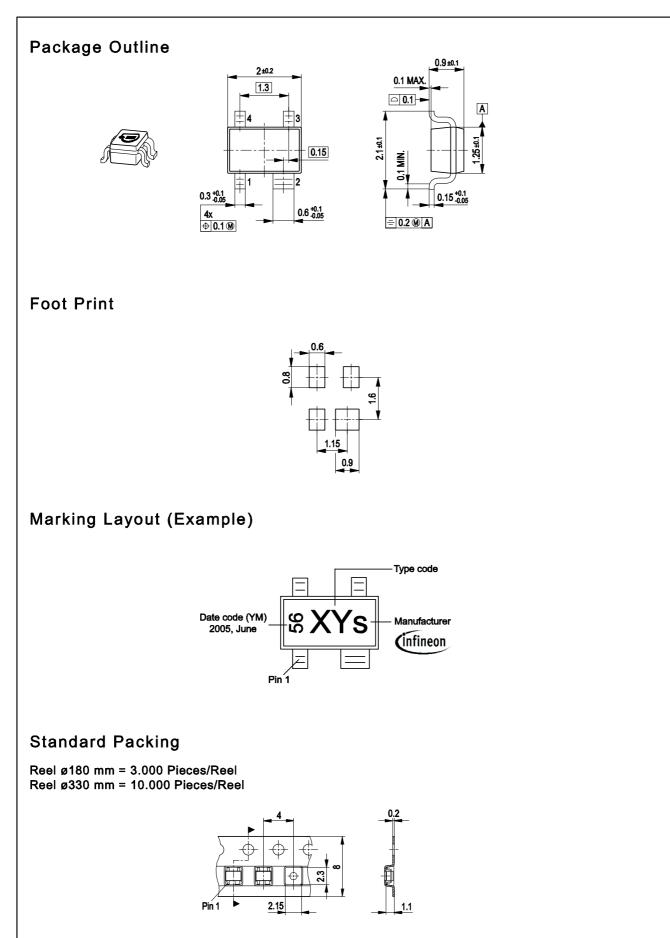


SPICE GP Model

For the SPICE Gummel Poon (GP) model as well as for the S-parameters (including noise parameters) please refer to our internet website www.infineon.com/rf.models.

Please consult our website and download the latest versions before actually starting your design. You find the BFP540 SPICE GP model in the internet in MWO- and ADS-format, which you can import into these circuit simulation tools very quickly and conveniently. The model already contains the package parasitics and is ready to use for DC and high frequency simulations. The terminals of the model circuit correspond to the pin configuration of the device. The model parameters have been extracted and verified up to 10 GHz using typical devices. The BFP540 SPICE GP model reflects the typical DC- and RF-performance within the limitations which are given by the SPICE GP model itself. Besides the DC characteristics all S-parameters in magnitude and phase, as well as noise figure (including optimum source impedance, equivalent noise resistance and flicker noise) and intermodulation have been extracted.









Edition 2009-11-16

Published by Infineon Technologies AG 81726 Munich, Germany

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